

(b) growing an intermediate layer on an uppermost lower well layer, the intermediate layer having a band gap broader than the lower well layer and a thickness thicker than the lower barrier layer;

(c) growing on the intermediate layer a lamination of alternately stacked upper well layer and upper barrier layer having a band gap broader than the upper well layer and a thickness thinner than the intermediate layer, to form an upper quantum well structure;

(d) forming a mask on the upper quantum well structure, the mask having periodical pattern;

(e) by using the mask as an etching mask, etching the upper quantum well structure in a periodical shape by using the intermediate layer as an etching margin layer; and

(f) removing the mask.